M ethods of quasiclassical G reen's functions in the theory of transport phenom ena in superconducting m esoscopic structures

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A bstract. A short introduction to the theory of matrix quasiclassical G reen's functions is given and possible applications of this theory to transport properties of mesoscopic superconducting-norm alm etal (S/N) structures are considered. We discuss a simplied version of these equations in the discusse are and in the case of a weak proximity elect. These equations are used for the calculation of the conductance of dierent S/N structures and for analysis of kinetic phenomena in these structures. We discuss the subgap conductance measured in SIN tunnel junctions and the mechanism of a nonmonotonic dependence of the conductance of a N wire on temperature T and voltage V, observed in an S/N structure.

Long-range, phase-coherent e ects are studied in a 4-term inal S/N/S structure under conditions when the Josephson critical current is negligible (the distance between superconductors is much larger then the coherence length in the norm alwire). It is shown that the Josephson e ects may be observed in this system if a current I, in addition to a current I₁ in the S/N/S circuit, ows through the N electrode.

1.Introduction

The progress of nanotechnology over the last few years has made it possible to produce conducting nanostructures in which new physical phenom ena have been observed. Speci cally, hybrid structures consisting of superconductors (S) and normal conductors (N) have been created using metal lm s [2{5] or sem iconductor layers [1,6{8] as the normal conductors. The transport properties of these S/N structures have turned out to be quite unusual. First, the subgap conductance (zero-bias anomaly) has been observed in SIN tunnel junctions at low temperatures (T < 100 m K) [1](see also [7,8]). Second, conductivity oscillations have been observed in these mesoscopic structures in a magnetic eld H (i.e., in structures with dimensions less then the phase-breaking length L,). O scillations of the con-

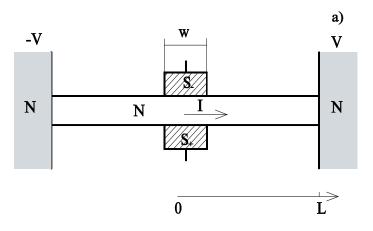
ductivity of the N channel appeared if the structure contained superconducting or norm al bops [2{6]. Moreover, for an N channel in contact with superconductors a nonm onotonic dependence of the conductivity on the tem perature T and voltage V has been observed at T T_{c} [5]. The main experimental facts have been explained in recent theoretical works (see review articles [23,24]). It was established that the proximity e ect plays the main role in the transport properties. For example, the conductivity of an N channel in the structure shown in Fig.1 changes as a result of the contribution of the condensate induced by the proximity e ect. Since the condensate is induced by both superconductors in a nonlocalm anner, interference R cos', which depends on the phase di erence ' between appears and a term the superconductors, arises in the resistance of the N channel $[9\{11]$. The phase di erence increases with the magnetic eld H, and this results in oscillations of the conductivity of the N channel in a magnetic eld. The nonmonotonic dependence of the resistance R of an N channel on T and V has also been explained [12[15] (see also the theoretical works in the Conference Proceedings in Ref. [14]). The nonmonotonic dependence of the resistance R (T;V) of a point contact ScN (c is a constriction) was rst obtained theoretically in Ref. [16].

New e ects have also been predicted in theoretical work devoted to S/N structures. For example, in Refs. [14,17] it was shown that the critical Josephson current I_c in a structure of the type displayed in Fig.1 depends on the voltage V_S between the S and N conductors, changing sign (- contact) if V_S exceeds a certain value. In addition, it has been shown that the Josephson e ect also arises in the case when current ows only through one S/N boundary. Several di erent con gurations of S/N structures were studied in Ref. [18], determ ining that under certain conditions the current-voltage characteristics of the S/N structures have descending segments (dI=dV < 0).

An important circum stance was noted in Ref. [19] (see also the works in Ref. [14]). It was shown that the local conductivity of an N channel changes over distances from the S/N boundary which can be much greater than the coherence length $_{\rm N}$ = D=2 T (D is the di usion coe cient). Important consequences follow from this fact. For example, phase coherence e ects in the conductivity of an N channel remain even if the distance 2L₁ between the superconductors is much greater than $_{\rm N}$. This means that the conductivity oscillations in the structure shown in Fig.1b will also be observed in the case of a negligibly low critical current I_c. The oscillation conservation e ect is due to fact that as T increases, I_c decreases exponentially (I_c exp($2I_{\rm F} = _{\rm N}$ (T)), and R decreases slow by (R T¹) [20,35].

In these lectures we discuss brie y the method of quasiclassical G reen's functions and apply this method to the study of transport phenomena in mesoscopic S/N structures. We restrict ourselves to the dirty limit where the mean free path 1 is essentially less than geometric dimensions of the system and the coherence length, but exceeds significantly the Ferm i wave length k_F (quasiclassic approximation). We will consider mostly a weak proximity elect, when the amplitude of the condensate induced in the norm almetal is small compared to the condensate amplitude in the superconductors S. This case occurs if the S/N interface resistance is larger than the resistance of the norm alconductor N. Results obtained for this case remain qualitatively valid in case when these resistances are comparable.

In the next Section we present them ain necessary equations for the G reen's functions and a general expression for the current in the N channel in which a condensate is present due to proxim ity e ect. In Section 3 we will give form ulas describing the subgap conductance of tunnel S/I/N junctions and discuss a possible physical interpretation of this conductance. In Section 4 we will consider the conductance of a N channel attached to two superconductors and obtain a form ula describing, in particular, the oscillatory behaviour of the conductance in an applied m agnetic eld H . A lso a nonmonotonic dependence of the conductance on temperature T and on bias voltage V will be analysed. The possibility of observing Josephson-like e ects in a S/N /S m esoscopic structure (see Fig.1b) will be considered in Section 5. W e will show that zero voltage between superconductors may exist in som e interval of the current through the S/N interfaces and Shapiro-steps may be observed even in absence of the real Josephson coupling between superconductors when the distance



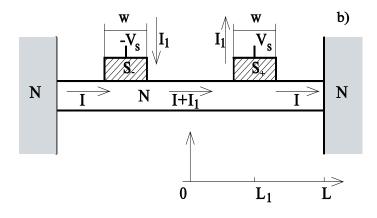


FIGURE 1. Schematic diagram of the system considered

separating superconductors exceeds essentially the coherence length

$$2L_1 N (T) = D = 2 T$$
: (1)

It is in portant that these e ects arise only in the case when a current I ow s along the N channel and the dissipation takes place [21,35].

2.Basic equations for quasiclassical G reen's functions

The G reen's function technique is a powerful tool for the theoretical study of di erent phenom ena in superconductors and superconducting structures. In the case of superconducting system s, we need to indroduce condensate G reen's functions of the type < $_{\rm w}$ (1) $_{\rm g}$ (2) >, therefore all the G reen's functions have a m atrix form. For example, the retarded (advanced) G reen's functions are de ned as follows [22,23]

$$\hat{G}^{R(A)} = (\underline{t}_{(2)}, \underline{t}_{(1)}) \hat{G}^{>} (1;2) \hat{G}^{<} (1;2)$$
 (2)

Here $\hat{G}^{<}$ and $\hat{G}^{>}$ are

$$\hat{G}^{>} = i < (1)^{+} (2) > (1)^{+1};$$

 $\hat{G}^{<} = i < ^{+} (2) (1) > (1)^{+1}$ (3)

We introduced here spin indices in the Nambu-space: $_1(1) = _*(1), _2(1) = _{\#}^+(1)$. As is well known, the functions $\hat{G}^{R(A)}$ describe the excitation spectrum of the system. In order to describe nonequilibrium processes, one needs to know the distribution functions which are related to the G reen's function \hat{G} indtroduced by K eldysh. It is convenient to de ne a supermatrix G (1;2) elements of which are the matrices $\hat{G}^{R(A)} = G(1;2)$ and $\hat{G} = G_{12}$. The element G_{21} is the zero matrix.

In the quasiclassical approximation all components of the G reen's functions G_{ex} (1;2) are integrated over the variable $_{p} = (p \quad p_{F})v_{F}$ and in the corresponding equation for G_{ex} (1;2) an expansion is carried out in the parameters $(p_{F} d)^{-1}$, $(p_{F} l)^{-1}$ or $(p_{F \ N})^{-1}$, where d is the thickness of the S or N $\ln s$, $_{N}$ is the coherence length in the N conductor and l is them can free path. The quasiclassical G reen's functions are de ned by the relation [22,23]

$$G (p=p;r;t_1;t_2) = (i=) d_p G_{ex} (p;r;t_1;t_2)$$
(4)

The subscript "ex" means exact (nonquasiclassical) G reen's functions. Therefore the quasiclassical G reen's functions G (1;2) depends on the angle of momentum on the Ferm i surface, on the coordinate r, and on two times.

In what follows we need an equation for the supermatrix G (1;2) only in the N conductor, having the form

$$Dr GrG + i _{z}; G = 0:$$
 (5)

where $_z$ is a diagonal supermatrix elements of which are the Pauli matrix z_z . Eq.(5) may be averaged over the thickness of the N lm d. Performing the averaging, we obtain

$$D Q_{x} G Q_{x}G + i _{z};G = b (x_{s}) G_{s};G :$$
(6)

where the coe cient $_{\rm b}$ is a characteristic energy which is proportional to the transmission of the S/N boundary: $_{\rm b}$ = $D = 2R_{\rm b2} d$, $R_{\rm b2}$ is the resistance of a unit area of the S/N boundary; and d are the resistivity and thickness of the N lm.

W hen deriving Eq. (6), the boundary condition

$$D \quad G \ \theta_z G = \left({}_b d_N \right)^h G ; G_S$$
(7)

was used. Here the z-axis is norm alto the plane of the S/N interface. The boundary conditions for the quasiclassical G reen's functions G have been derived in the general case by Zaitsev [25] and have been reduced to the simple form (7) by Kupriyanov and Lukichev [26] in the dirty case. In the case of a good S/N contact, condition (7) is reduced to the continuity of the G reen's functions at the S/N interface: $G = G_s$. In the case of a poor contact $(_b ! 0)$, condition (7) gives the same result for the current through the S/N interface as obtained with the aid of the tunneling Ham iltonian method. However, for a S/N contact with an arbitrary barrier transparency condition (7) is not applicable. The point is that when deriving Eq. (7) Kupriyanov and Lukichev [26] restricted them selves to the Legendre polynom ials of the zeroth and st orders in the expansion of the angle-dependent G reen's function G. M eanwhile, one can easily show that all the Legendre harmonics are excited near the S/N (or N/N 0) interface. They decay to zero (except the Legandre polynomials of the zeroth and rst order) over the mean free path away from the interface. In order to obtain a correction of the next order in $_{\rm b}$ to condition (7), one has to solve an integral equation (see Ref. [27]). In the case of the S/N interface with an arbitrary barrier transparency, the problem of boundary conditions for the quasiclassical G reen's functions becomes complicate (boundary conditions and their applicability are discussed in detail in the Raim ondi's Lecture Notes).

Eq.(6) must be solved in the normal conductor for a particular geometry (see, for example, Fig.1) with boundary conditions at x = L. In the case of normal reservoirs the condensate functions $\hat{F}^{R(A)}$ (L) are equal to zero and $\hat{G}^{R(A)}$ (L) =

 $^{\rm a}_{\rm z}$. In the case of superconducting reservoirs the boundary conditions for the retarded (advanced) G reen's functions are

$$\hat{\mathbf{G}}^{\mathrm{R}(\mathrm{A})}(\mathrm{L}) = \mathbf{G}^{\mathrm{R}(\mathrm{A})}_{\mathrm{Z}} + \hat{\mathbf{F}}^{\mathrm{R}(\mathrm{A})}_{\mathrm{S}}$$
(8)

 $\underset{q}{\overset{\text{here } G^{R(A)}}{(i)}} = \underset{q}{\overset{R(A)}{)}} = \underset{q}{\overset{R(A)}{)}} = \underset{q}{\overset{R(A)}{(i_x \sin + i_y \cos)}} ; \overset{R(A)}{(i)} = \underset{q}{\overset{R(A)}{(i)}} = \underset{R(A)}{(i)} = \underset{R(A)$

between superconductors 2V is much less than =e. We assume that there is no barrier between the N conductor and reservoirs.

The Keldysh function $\hat{\mathsf{G}}$ describes the kinetic properties of the system and is related to distribution functions

$$\hat{\mathbf{G}} = \hat{\mathbf{G}}^{\mathrm{R}} \hat{\mathbf{f}} \quad \hat{\mathbf{f}} \hat{\mathbf{G}}^{\mathrm{A}} \tag{9}$$

where $\hat{f} = f_o \hat{1} + f_z^{*}$ is a matrix distribution function. The function f_o enters an expression for the supercurrent (in a superconductor it determ ines the energy gap), and the function f determ ines the quasiparticle current (in a superconductor it describes the charge-in balance and the electric eld; see, for example [28]). In reservoirs the functions f_o and f are supposed to have equilibrium form

$$f_{o}(L) = [tanh((+eV)) + tanh((eV))]=2;$$
 (10)

$$f(L) = tanh((+eV)) tanh((eV))=2;$$
 (11)

where $= (2T)^{1}$.

If the functions $\hat{G}^{R(A)}$ and \hat{G} are known, one can easily nd a relation between the applied voltage 2V and the current I in the N conductor. The expression for the current is [22,23]

$$I = (d=8)Tr_{z}^{2} d \hat{G}^{R} \theta_{x}\hat{G} + \hat{G} \theta_{x}\hat{G}^{A})$$
(12)

Eqs.(6) and (12) can be simplied signicantly in the case of a weak proximity e ect when the amplitudes of the condensate functions in the N conductor $\mathbf{F}^{R,(A)}$ are small. Then the retarded (advanced) G reen's functions in the N conductor have the form

$$\hat{\mathbf{G}}^{\mathrm{R}(\mathrm{A})} = \mathbf{G}^{\mathrm{R}(\mathrm{A})} \hat{\mathbf{z}} + \mathbf{F}^{\mathrm{R}(\mathrm{A})}$$
(13)

where $G^{R(A)}$ [1 + $(F^{R(A)})^2 = 2$] and $jF^{R(A)}j$ 1. When obtaining the relation between $\hat{G}^{R(A)}$ and $\hat{F}^{R(A)}$, we employed the norm alization condition [22,23]

$$(G^{R(A)})^{2}\hat{1} + (\hat{F}^{R(A)})^{2} = \hat{1};$$
(14)

where $\hat{1}$ is a unit matrix.

The equation for the condensate functions $\mathbf{F}^{\mathbf{R}(A)}$ follows from Eq.(6) and the expression (14)

$$\mathbb{Q}_{xx} \hat{F}^{R(A)} \qquad k^{R(A)} \hat{F}^{R(A)} = k^{2} \hat{F}^{R(A)} = k^{2} \hat{F}^{R(A)} (x - L_{1}) + \hat{F}^{R(A)}_{S} (x + L_{1})$$
(15)

where $k_b^2 = 2_b = D$; $k^{R(A)}^2 = (2i +) = D$, w is the width of the S/N interface in the x-direction and is supposed to be much less than L and _N (T). We introduce here the depairing rate in the N conductor which determ ines the phase-breaking

length L = D = .0 not the functions $F^{R(A)}$ are known from a solution of the linear equation (15), we can define the conductance of the N lm.

Let us consider for example the system shown in Fig.1.W riting down Eq.(6) for the matrix element (12), we arrive at the equation outside the S/N interface

$$D \, \varrho_x \stackrel{h}{G} \, \varrho_x G + G \, \varrho_x G^{A} \stackrel{i}{} + i \stackrel{h}{} \, {}^{z}_{z}; G^{i} = 0; \qquad (16)$$

M ultiplying Eq.(16) by $\ensuremath{\,^{}_{z}}$ and calculating the trace, we obtain after the $\ensuremath{\,^{\rm rst}}$ integration

$$(\mathfrak{Q}_{\mathbf{x}}\mathbf{f}) [1 \quad \mathbf{m}] = \mathbf{J}():$$
 (17)

Here J () is an x-independent constant and

$$m = (1=8) \operatorname{Tr} \hat{F}^{R} \hat{F}^{A^{2}}$$
(18)

is a function which describes the condensate contribution to the N $\,$ In conductance. The left side of Eq.(17) stems from the rst term in the square brackets in Eq.(16) provided that the condensate functions are sm all. Therefore, according to Eq.(12), the current I is an integral from the "partial current" J

$$I = (d=2)^{2} d J ()$$
 (19)

Solving Eq.(17) with boundary conditions (11), we can discrete nd a relationship between the current and voltage I (V). In the next Sections we will analyse the conductance of S/N m esoscopic systems.

3.Subgap conductance in SIN junctions

In this Section the subgap conductance in superconductor/insulator/norm alm etal (S/I/N) tunnel junctions will be discussed. As is well known from conventional theory for S/I/N junctions, the subgap conductance should exponentially decrease with decreasing tem perature T (see, for example, Ref. [29]). However, experiments on Nb/n+ InG aA s contacts have established that a peak in conductance appears at zero-bias if the tem perature becom es low enough (T), and the magnitude of this peak at low tem peratures (T 50 m K) is comparable with the conductance in the normal state [1]. This contact can be considered as a tunnel S/I/N junction. A Schottky barrier at the interface plays the role of the insulating layer I. An explanation for anom abus transparency of the SIN junction at low voltages and tem peratures (T;eV) was suggested in Refs. [9,30{34]. According to the interpretation proposed in R ef. [32], the subgap conductance is due to a component of the current which, in the case of a SIS Josephson junction, gives the so-called interference current. This component can be presented in the form

$$I_{int} = (8R_b)^{1} d'' F' ('';V) F^{R} + F^{A} F^{R}_{S} + F^{A}_{S};$$
(20)

where F_N (";V) is defined in Eq. (11); $F_S^{R(A)} = =$ (" i)² ² ¹⁼² are the condensate, retarded (advanced) G reen's functions in the superconductor. This form ula can be obtained from the general expression for the current (12) and from Eq.(6) in which we have to put $(x_s) = 1$. If the energy " is small, $F^R = F^A$

i. In the case of a S/I/N junction, $F^{R(A)}$ are the condensate functions in the N electrode. To zero order in the barrier transm ittance (i.e., in R_b^{-1}), they are equal to zero. If the proximity e ect is taken into account, they dier from zero and in the case of a planar S/I/N junction they have the form (see, for example, Ref. [32])

$$F^{R(A)} = {}^{k}_{b} = (" i); > "_{b}$$

$$F^{R(A)} = {}^{h}_{b} = (" i)^{2}_{b} {}^{2}_{b} = (" i)^{2}_{b} = (" i)^{2}_{b} {}^{2}_{b} = (" i)^{2}_{b} = (" i)^$$

This form ula can be obtained from Eq.(6) in the case of weak and strong proximity e ect. It is seen from Eq.(21) that $F^{R(A)}$ are small if "b "; , where " is determined either by temperature T or voltage V. In the opposite limit when " and are small compared with "b, $F^{R(A)}$ are not small, and the di erential conductance normalized by R_b^{-1} , $S = R_b dI = dV$, calculated from Eq.(20) for T = 0 and V = 0 is not small either. The integrand in Eq.(20) is not zero if J''_{J} because $F^{R} = F^{A}$ at J''_{J} and $F^{R} = F^{A}$ at J''_{J} . This means that the current given by Eq.(1) is caused by the charge-transfer mechanism of the same type as Andreev re ection processes. The second in portant circum stance leading to the subgap conductance is related to an anom alous proximity e ect when the am plitude of the condensate functions $F^{R(A)}$ at small energies " is not small.

The density-of-states (DOS) in the N electrode is changed drastically in the case of the strong proximity e ect: the DOS is zero at j $\not>$ b and the DOS = $= \frac{2}{2} = \frac{2}{b}$ in the interval $j \Rightarrow$ b. In a one-dimensional S/I/N junction the DOS has a quasigap at j $\not>$ b. In both cases of a planar or one-dimensional S/I/N junctions the zero-bias, zero-tem perature conductance coincides with it's value in the norm all state [32].

4.C onductance of the Andreev interferom eter

Consider the system shown in Fig.1 (the Andreev interferom eter). In order to calculate the norm alized di erential conductance of the N channelS = $R_N dI=vV$ in the presence of a phase di erence between superconductors, we must solve Eq.(17) taking into account the boundary condition (11). The function m is small by assumption. Therefore the expression for J may be presented in the form

$$J() = F_N(;V) [1 m i]=L$$
 (22)

where hm $i = (1=L)_{0}^{R_{L}} dx \quad \hat{m}$. Substituting (22) into Eq.(19), we can obtain an expression for S. Here we present the formula for a deviation of the normalized dimension ductance from it's value in the normal state R_{N} : S (2L = d) dI=dV 1. We obtain

$$S = (1=2) d \int_{N}^{0} F; V h i;$$
 (23)

where F_N^0 (;V) = \cosh^2 (+ eV) + \cosh^2 (eV) = 2. By virtue of the definition of lm i (see Eqs.(18)), we can write lm i in the form

hm
$$i = Tr \dot{F}^{R}^{2} + \dot{F}^{A}^{2} \dot{F}^{R} \dot{F}^{A} = 8$$
 (24)

The rst two terms in (24) determ ine a change in the DOS of the N channel due to the condensate (this term reduces the conductance), and the last, so-called anom alous, term leads to an increase of the conductance.

As it is seen from Eq.(23), in order to nd the conductance, we need to solve Eq.(15) for the condensate functions $\hat{F}^{R(A)}(x)$. In this Section we present here the solution for the geometry shown in Fig.1a.

$$\mathbf{\hat{F}}^{R(A)}(\mathbf{x}) = \mathbf{i}_{y}^{R} \mathbf{F}_{s}^{R(A)} \mathbf{r}^{h} \mathbf{r}^{R(A)} \cosh^{R(A)} \sinh^{h} \mathbf{k}^{R(A)} (\mathbf{L} \mathbf{j} \mathbf{x} \mathbf{j}) \cos' \qquad (25)$$

Here $r = k_0^2 Lw$ is the ratio of the N channel resistance to the S/N resistance, $R(A) = k^{R(A)}L.Calculating hm$ i.we nd

$$\text{Im i} = r^2 = 8 \quad \text{Re}[\sinh(2) = 2 \quad 1] = (\cosh^2) \quad [\sinh(2_1) = 2_1 \\ \sin(2_2) = 2_2] = j \quad \text{coth} \quad 2 \quad (1 + \cos 2')$$
 (26)

where = $_1 + i_2$. The rst term in (26) determ ines a contribution to the conductance due to a change in the DOS, and the second term is related to the anom abus term ($\hat{F}^A \hat{F}^R$). In Fig.2 we show the dependence S_{DOS} (rst term contribution) and the S_{an} (V) dependence (anom abus term contribution) at T = 0. It is seen that S_{DOS} (V) is negative and S_{an} (V) is positive. The total change in the conductance S (V) = S_{DOS} (V) + S_{an} (V) is shown by the solid line. This quantity increases with increasing V from zero, reaches a maximum at V_m $_L$ = e, and decays to zero with further increase of V (here $_L = D = L^2$ is the so-called Thouless energy).

As follows from (23) and (26), the conductance S oscillates with increasing the phase di erence. In Fig.2 we also plot the tem perature dependence of the zero-bias conductance. Both curves, S(V) at T = 0 and S(T) at V = 0 are similar. Note that nonmonotonous tem perature dependence of the conductance was obtained earlier in Ref. [16] where a short ScN contact was analyzed (here cm eans a constriction).

5.D issipative Josephson-like e ects in S/N/S structures In this Section we discuss a possibility to observe Josephson-like e ects in mesoscopic S/N/S structures (see Fig.1b) with negligible Josephson coupling between superconductors, i.e., when the inequality (1) is fulled [21,35]. Following the same steps as in Section 2, we obtain instead of Eq.(17)

$$(1 m (x)) \theta_{x} f = \begin{matrix} (J + J_{1} & J_{2}; & 0 < x < L_{1} \\ J; & L_{1} < x < L \end{matrix}$$
(27)

In what follows the function m plays the most important role.

The current on the segment $(0, L_1)$ is determined by Eq.(19) if J is replaced by $J + J_1$. The quantity J_S , the superconducting \current", is constant over the segment (L_1, L) and $(0, L_1)$ and is equal to

$$J_{\rm S} = (1=4) \,\mathrm{Tr}_{z}^{2} \,\hat{\mathrm{F}}^{\mathrm{R}} \,\theta_{\rm x} \hat{\mathrm{F}}^{\mathrm{R}} \,\hat{\mathrm{F}}^{\mathrm{A}} \,\theta_{\rm x} \hat{\mathrm{F}}^{\mathrm{A}} \tag{28}$$

The integral of J_s (28) over the energy is exponentially small if the condition (1) is satistical. As follows from Eq. (6), the constant J_1 , is related with the G reen's function and distribution function in the superconductor. It can be written in the form [11]

$$J_{1} = J_{q} + J_{S}; J_{q} = (=d_{N} <_{b}) [F_{S} () f (I_{2})]$$
(29)

Here $<_{b} = R_{b2} = w_{N-S}^{h} + (1=8) \operatorname{Tr} \hat{F}^{R} + \hat{F}^{A} + \hat{F}^{R}_{S} + \hat{F}^{A}_{S}^{h}$ is the resistance of the S/N boundary per unit length in the y direction and N, S^{-} are the density of states in the N and S conductors. It can be shown that for $V_{N,S}$ which are small compared with T=e, the \supercurrent" J_{S}^{*} , owing throw the S/N boundary equals J_{S} . The distribution function F_{S} is the equilibrium function, i.e., it is identical to the function in Eq. (11), if V_{N} is replaced by V_{S} (we measure voltages from the point 0, where the voltage is equal to zero). Using the fact that m is small, we can integrate Eq. (27) and nd the relation of J and J_{q} with F_{N} and F_{S} (see the boundary condition (11)). We obtain the norm al currents

$$(d_{N} =) J = \frac{\langle {}_{b}F_{N} + \langle {}_{1}(F_{N} - F_{S}) \rangle}{\langle {}_{b}\langle {}_{+} + \langle {}_{1}\langle {}_{2}\rangle};$$

$$(d_{N} =) J_{1} \qquad J_{I}(d_{N} =) = \frac{\langle {}_{2}F_{S} + \langle {}_{1}(F_{S} - F_{N}) \rangle}{\langle {}_{b}\langle {}_{+} + \langle {}_{1}\langle {}_{2}\rangle}$$
(30)

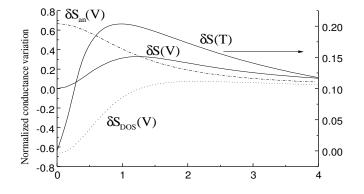


FIGURE 2. Normalized conductance S vs. normalized voltage eV = L at T = 0 and vs. normalized temperature T = L at V = 0 for the structure shown in Fig.1a.

Here $<_{b}$ is determined in Eq. (29); the quantity $< = <_{1} + <_{2}, <_{1;2} = R_{1;2}$ (1 + hm i) can be term of the partial resistance. The spatial average hm $i_{1;2}$ on the segments (0, L_{1}) and (L_{1} , L) gives a decrease in the resistances on account of proximity e ect (m i is negative). All resistances in Eq. (30) depend on the di erence of the phases ' and on the energy; they can be represented in the form $<_{b} = R_{b} <_{b} \cos '$ and $<_{1;2} = R_{1;2} <_{1;2} \cos '$. The corrections to the resistances $<_{b}$ and $<_{1;2}$ are small in the case of a weak proximity e ect. The quantities R_{b} and $R_{1;2}$, depend, generally speaking, on the energy (for example, s depends on). We assume, for sim plicity, that these quantities do not depend on the energy. This is valid if it is assumed that the superconductors are gapless (the results remain qualitatively the same in the case of superconductors with a gap). Then, integrating Eq. (30) over energies, we obtain on the left-hand side the currents I and I₁ (see Eq. (19)). E lim inating V_N from the two equations obtained, we nd for V_S

$$V_{s} = h \theta_{t}' = 2e =$$

$$I_{1} [R_{b} + R_{1} (R_{b} + R_{1}) \cos 2'] + I (R_{1} - R_{1} \cos 2')$$
(31)

Here we employed the Josephson relation; R_b is the resistance of the S/N boundary, which in the case of zero-gap superconductors is approximately equal to its value in the normal state. The resistance R_1 is also approximately equal to $L_1=d_N$ (the '-independent correction arising from hm i is small and unimportant). Integrating Eq. (31), we obtain a relation between the average voltage V_S and the xed currents I and I_1 .

$$V_{\rm S} = \frac{q}{\left[(I + I_1)R_1 + I_1R_b\right]^2} \quad \left[(I + I_1)R_1 + I_1R_b\right]^2 \quad (32)$$

The function V_s (I₁) is displayed in Fig.3 for di erent currents I. One can see that for I \notin 0 this dependence is identical to the current-voltage characteristic of a standard Josephson contact. In this case the critical current is

$$I_{c} = I \frac{R_{1}R_{b}}{(R_{b} + R_{1})^{2}}$$
(33)

Therefore I_c increases in proportion to the current I. We shall show below that the correction R_1 decreases slow by with increasing temperature (R_1 T¹), and the correction R_b is small if the condition (1) is satisticed. Therefore, for R_b R_1 , we obtain I_c ' I $R_1=R_b$. The maximum current I is limited by the condition that Joule heating be small and by the condition eV_N ' eIR T. In the opposite case R_1 decreases as V_N increases. If the condition (1) is not satisted and a nite Josephson coupling exists between the superconductors, then it is easy to show that the critical current of the structure equals $I_c = I_c^2 + I_{col}^2$, where I_{col} is the critical Josephson current. An expression for I_{col} can be easily obtained with the aid of Eq. (28). This expression is presented in Ref. [20]. The equilibrium phase di erence '₀ for $I_1 + IR_1 = (R_b + R_1) = 0$ equals 2'₀ = $\arcsin(I_c = I_c)$. To determ ine R_1 and R_b it is necessary to nd the condensate functions $\mathbf{F}^{\mathbf{R}(A)}$, For $\mathbf{j}\mathbf{x}\mathbf{j} < L_1$ the solution of Eq.(15) has the form

$$\mathbf{F}^{\mathrm{R}(\mathrm{A})}(\mathbf{x}) = \mathbf{F}_{\mathrm{s}}^{\mathrm{R}(\mathrm{A})} \left[\mathrm{i}_{\mathrm{y}}^{\mathrm{cos}}(\mathbf{x}) + \mathrm{i}_{\mathrm{y}}^{\mathrm{cosh}}(\mathbf{x}) + \mathrm{i}_{\mathrm{x}}^{\mathrm{sin}}(\mathbf{x}') + \mathrm{i}_{\mathrm{x}}^{\mathrm{sin}}(\mathbf{x}) \right]^{\mathrm{R}(\mathrm{A})}$$
(34)

Here $F_{s}^{R(A)}$ is the amplitude of the condensate functions in the superconductors. In the zero-gap case $F_{s}^{R(A)} = = (i_{s})$, where s is the frequency of spin- ip collisions with in purities. The functions $P_{x,y}$ equal: $P_{x} = bsinh_{2} = (sinh_{1} + bsinh_{1} sinh_{2})$, $P_{y} = bsinh_{2} = (cosh_{1} + bcosh_{1} sinh_{2})$, $b = w = (R_{b2} d_{N}) k$, $k^{R(A)} = \frac{q}{2i} = D$, = 1 + 2, $1;2 = \frac{0}{1;2} + i \frac{0}{1;2} = kL_{1;2} O nce$ the functions $F^{R(A)}$ are known, the interference correction R_{1} to the resistance can be calculated:

$$R_{1} = R_{1} d \cos^{2}()hm (x;') m (x; =2)i_{1}$$
(35)

W ith the aid of the expressions for Im i_1 and for $\hat{F}^{R(A)}$ (see Eq. (34)), we nd

$$R_{1} = R_{1} = d \cos^{2}(M(t);$$
(36)

where M () = $(1=8)_{1}^{n} f_{s}^{2} \int_{1}^{2} f_{y}^{2} \int_{1}^{2} (\sinh (2_{h}^{0}) = 2_{1}^{0} + \sin (2_{1}^{0}) = 2_{1}^{0})$ $f_{x}^{2} \int_{1}^{2} (\sinh (2_{1}^{0}) = 2_{1}^{0}) \sin (2_{1}^{0}) = 2_{1}^{0} + ReF_{s}^{2} P_{y}^{2} (\sinh (2_{1}) = 2_{1} + 1)$

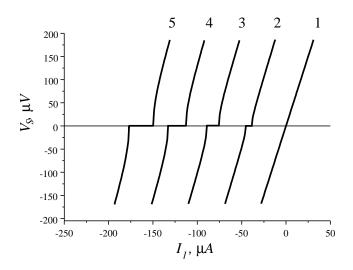


FIGURE 3. V_S versus the current I_1 for the following values of the current: 1 - 0, 2 - 250 A, 3 - 500 A, 4 - 750 A, 5 - 1m A. Here $R_1 = 0.1R_1, R_b = 5R_1, R_1 = 1$.

 P_x^2 (sinh (2₁)=2₁ 1)]. The temperature dependence of R₁ is displayed in Fig.4. One can see that for T > $_{L_1} = D = (2L_1)^2$ the quantity R₁ decreases as T⁻¹ with increasing temperature. As noted in Refs. [15,18], the slow decrease of R₁ (T) is due to the so-called anom alous term F_RF_A in lm i_1 . The special role of this term, which is nonanalytic both in the upper and lower planes of , was noted in Ref. [36].

The Josephson current I_S is determined by the integral of J_S (28), over all energies, i.e., the integral of products of either advanced or retarded G reen's functions. It can be calculated by closing the integration contour in the upper (low er) halfplane of and switching to sum m ation over the M atsubara frequencies $!_n = T (2n + 1)$. For such energies the functions $F^{R(A)}$ decay exponentially over distances k¹ (!_n) n (T) away from the S/N boundary. Therefore the current $I_{\rm S}$ will be exponentially small ($I_{\rm S}$ exp ($2I_{H} = N$ (T)). The function I_{S} (T) for the structure shown in Fig.1b is presented in Ref. [20]. Sim ilar arguments are also applicable to the calculation of R_b , since for T < s the functions F_s^R and F_s^A can be assumed to be equal and independent of the energy. At the same time, the function $F^{R}F^{A}$, appearing in the expression for R_{1} , decreases over a small (com pared with T) energy $L_1 = D = (2L_1)^2$ and makes a nonzero contribution. For such energies the characteristic decay length of $F^{R(A)}(x)$ is of the order $L_{1,i}$ i.e., of the order of the distance between the superconductors.

In order to observe long-range Josephson e ects, the critical current I_c must exceed the uctuation current $Te=h: I_c$ $Te=h. On the other hand, the ordinary Josephson e ect is negligible if the condition <math>_{L_1}$ T is full led. Combining these inequalities, we obtain the condition

$$TR_{b}R_{1} = (R_{b}R_{Q}) \qquad L_{1} \qquad (37)$$

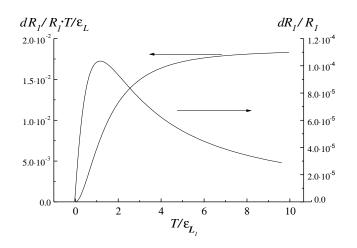


FIGURE 4. Interference correction R_1 to the resistance as a function of temperature in the case $L_1 = 0.5L$, $R = R_b = 0.4$, = L = 100, = L = 30.

which should be satis ed for observation of the e ects under consideration. Here $R_Q = h = e^2$ 3k, and we took into account that a maximal value of I is determined by the relation eIR L_1 . O therwise R_1 decreases with increasing I. The rst inequality of (37) means that the zeroth Shapiro step on the I_1 (V_S) curve is absent at I = 0. If the second inequality of (37) is not fullled, then the critical current is not zero at I = 0 (ordinary Josephson e ect). In this case the e ective critical current I_c should rst increase with increasing I and then decrease when I exceeds $L_1 = \mathbb{R}$.

6.Conclusion

In conclusion we note that, as one can see from Fig.4, the correction R_1 to the resistance of the norm al channel caused by the proximity e ect depends on the tem perature T in a nonmonotonic way: it is equal to zero at T = 0 (the bias voltage is zero as well), reaches a maximum at T $_{L_1}$ and decays to zero at higher T. Such behavior of R_1 (T) is related, as noted in [15], to di erent dependencies of two contributions to R_1 on the energy . One contribution which increases the N channel resistance is connected with a decrease of the density-of-states in the norm alchannel, which is described by the last term in M () (see Eq. (36)). Another contribution (anom alous) which dim inishes the resistance of the norm al channel is described by the rst two terms in M (). This contribution exactly compensates a contribution due to a change in the density-of-states of the norm alchannel = 0and dominates at Θ 0. At T > T_c it leads to the M aki-Thom pson contribution to the paraconductivity. M athem atically, compensation of the two contributions at = 0 arises because at = $0 F^{R} = F^{A}$ and m in Eq. (35) tends to zero. The nonmonotonic behavior of R has been observed in an experiment [5]. It would be interesting to observe the long-range Josephson e ect experim entally.

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